Single 2-Input NAND Gate/ CMOS Logic Level Shifter

LSTTL-Compatible Inputs

The MC74VHC1GT00 is a single gate 2–input NAND fabricated with silicon gate CMOS technology.

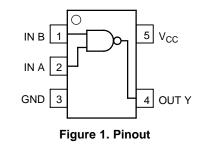
The internal circuit is composed of multiple stages, including a buffer output which provides high noise immunity and stable output.

The device input is compatible with TTL-type input thresholds and the output has a full 5 V CMOS level output swing. The input protection circuitry on this device allows overvoltage tolerance on the input, allowing the device to be used as a logic-level translator from 3 V CMOS logic to 5 V CMOS Logic or from 1.8 V CMOS logic to 3 V CMOS Logic while operating at the high voltage power supply.

The MC74VHC1GT00 input structure provides protection when voltages up to 7 V are applied, regardless of the supply voltage. This allows the MC74VHC1GT00 to be used to interface 5 V circuits to 3 V circuits. The output structures also provide protection when $V_{CC} = 0$ V. These input and output structures help prevent device destruction caused by supply voltage – input/output voltage mismatch, battery backup, hot insertion, etc.

Features

- High Speed: $t_{PD} = 3.1$ ns (Typ) at $V_{CC} = 5$ V
- Low Power Dissipation: $I_{CC} = 1 \ \mu A$ (Max) at $T_A = 25^{\circ}C$
- TTL–Compatible Inputs: $V_{IL} = 0.8 V$; $V_{IH} = 2 V$
- CMOS–Compatible Outputs: $V_{OH} > 0.8 V_{CC}$; $V_{OL} < 0.1 V_{CC}$ @Load
- Power Down Protection Provided on Inputs and Outputs
- Balanced Propagation Delays
- Pin and Function Compatible with Other Standard Logic Families
- Chip Complexity: FETs = 64
- Pb–Free Packages are Available



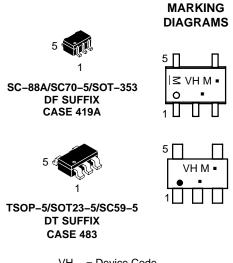






ON Semiconductor®

http://onsemi.com



VH = Device Code

```
M = Date Code*
```

= Pb–Free Package

(Note: Microdot may be in either location) *Date Code orientation and/or position may vary depending upon manufacturing location.

PIN ASSIGNMENT				
1	IN B			
2	IN A			
3	GND			
4	OUT Y			
5	V _{CC}			

FUNCTION TABLE

Inp	uts	Output
Α	в	Y
L	L	Н
L	н	Н
н	L	Н
Н	Н	L

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.

Semiconductor Components Industries, LLC, 2007 February, 2007 – Rev. 11

MAXIMUM RATINGS

Symbol	Ch	aracteristics	Value	Unit
V _{CC}	DC Supply Voltage		-0.5 to +7.0	V
V _{IN}	DC Input Voltage		-0.5 to +7.0	V
V _{OUT}	DC Output Voltage	V _{CC} = 0 High or Low State	–0.5 to 7.0 –0.5 to V _{CC} + 0.5	V
I _{IK}	Input Diode Current		-20	mA
I _{OK}	Output Diode Current	V _{OUT} < GND; V _{OUT} > V _{CC}	+20	mA
I _{OUT}	DC Output Current, per Pin		+25	mA
Icc	DC Supply Current, V _{CC} and GND		+50	mA
T _{STG}	Storage Temperature Range		-65 to +150	°C
ΤL	Lead Temperature, 1 mm from Case	for 10 Seconds	260	°C
TJ	Junction Temperature Under Bias		+ 150	°C
θ_{JA}	Thermal Resistance	SC70–5/SC–88A/SOT–353 (Note 1) SOT23–5/TSOP–5/SC59–5	350 230	°C/W
PD	Power Dissipation in Still Air at 85°C	SC70–5/SC–88A/SOT–353 SOT23–5/TSOP–5/SC59–5	150 200	mW
MSL	Moisture Sensitivity		Level 1	
F _R	Flammability Rating	Oxygen Index: 28 to 34	UL 94 V–0 @ 0.125 in	
V _{ESD}	ESD Withstand Voltage	Human Body Model (Note 2) Machine Model (Note 3) Charged Device Model (Note 4)	>2000 >200 N/A	V
I LATCHUP	Latchup Performance	Above V _{CC} and Below GND at 125°C (Note 5)	±500	mA

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. Measured with minimum pad spacing on an FR4 board, using 10 mm-by-1 inch, 2-ounce copper trace with no air flow.

2. Tested to EIA/JESD22-A114-A.

3. Tested to EIA/JESD22-A115-A.

4. Tested to JESD22-C101-A.

5. Tested to EIA/JESD78.

RECOMMENDED OPERATING CONDITIONS

Symbol	Characteristics		Min	Max	Unit
V _{CC}	DC Supply Voltage		3.0	5.5	V
V _{IN}	DC Input Voltage		0.0	5.5	V
V _{OUT}	DC Output Voltage High of	VCC = 0 Low State	0.0 0.0	5.5 V _{CC}	V
T _A	Operating Temperature Range		-55	+125	°C
t _r , t _f	Input Rise and Fall Time $V_{CC} = 3.$ $V_{CC} = 5.$	3 V ± 0.3 V 0 V ± 0.5 V	0 0	100 20	ns/V

Device Junction Temperature versus Time to 0.1% Bond Failures

Junction Temperature °C	Time, Hours	Time, Years
80	1,032,200	117.8
90	419,300	47.9
100	178,700	20.4
110	79,600	9.4
120	37,000	4.2
130	17,800	2.0
140	8,900	1.0

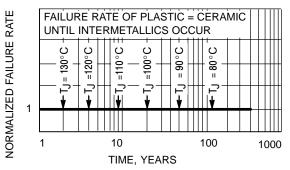


Figure 3. Failure Rate vs. Time Junction Temperature

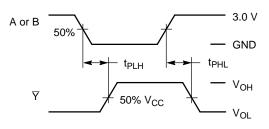
DC ELECTRICAL CHARACTERISTICS

			v _{cc}	Т	A = 25°	С	T _A ≤	85°C	–55 ≤ T _A	≤ 125°C	
Symbol	Parameter	Test Conditions	(V)	Min	Тур	Max	Min	Мах	Min	Max	Unit
V _{IH}	Minimum High–Level Input Voltage		3.0 4.5 5.5	1.4 2.0 2.0			1.4 2.0 2.0		1.4 2.0 2.0		V
V _{IL}	Maximum Low–Level Input Voltage		3.0 4.5 5.5			0.53 0.8 0.8		0.53 0.8 0.8		0.53 0.8 0.8	V
V _{OH}	Minimum High–Level Output Voltage V _{IN} = V _{IH} or V _{II}	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $I_{OH} = -50 \ \mu \text{A}$	3.0 4.5	2.9 4.4	3.0 4.5		2.9 4.4		2.9 4.4		V
		$V_{IN} = V_{IH} \text{ or } V_{IL}$ $I_{OH} = -4 \text{ mA}$ $I_{OH} = -8 \text{ mA}$	3.0 4.5	2.58 3.94			2.48 3.80		2.34 3.66		V
V _{OL}	Maximum Low-Level Output Voltage	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $I_{OL} = 50 \ \mu\text{A}$	3.0 4.5		0.0 0.0	0.1 0.1		0.1 0.1		0.1 0.1	V
	$V_{IN} = V_{IH}$ or V_{IL}		3.0 4.5			0.36 0.36		0.44 0.44		0.52 0.52	V
I _{IN}	Maximum Input Leakage Current	$V_{IN} = 5.5 V \text{ or GND}$	0 to 5.5			±0.1		±1.0		±1.0	μΑ
I _{CC}	Maximum Quiescent Supply Current	$V_{IN} = V_{CC}$ or GND	5.5			1.0		20		40	μA
I _{CCT}	Quiescent Supply Current	Input: V _{IN} = 3.4 V	5.5			1.35		1.50		1.65	mA
I _{OFF}	Power Off Output Leakage Current	V _{OUT} = 5.5 V	0.0			0.5		5.0		10	μA

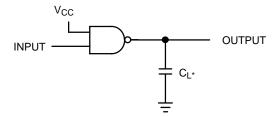
AC ELECTRICAL CHARACTERISTICS Input $t_r = t_f = 3.0 \text{ ns}$

				Т	A = 25°	С	T _A ≤	85°C	$-55 \le T_A$	≤ 125°C	
Symbol	Parameter	Test Condi	tions	Min	Тур	Max	Min	Max	Min	Max	Unit
t _{PLH} , t _{PHL}	Maximum Propagation Delay, Input A or B to Y	$V_{CC} = 3.3 \pm 0.3 \text{ V}$	C _L = 15 pF C _L = 50 pF		4.1 5.5	10.0 13.5		11.0 15.0		13.0 17.5	ns
		$V_{CC} = 5.0 \pm 0.5 \text{ V}$	$C_L = 15 \text{ pF}$ $C_L = 50 \text{ pF}$		3.1 3.6	6.9 7.9		8.0 9.0		9.5 10.5	
C _{IN}	Maximum Input Capacitance				5.5	10		10		10	pF
					1	Typical	@ 25°C	, V _{CC} =	5.0 V		
CPD	Power Dissipation Capacita	ance (Note 6)					11				рF

6. C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: $I_{CC(OPR)} = C_{PD} \bullet V_{CC} \bullet f_{in} + I_{CC}$. C_{PD} is used to determine the no-load dynamic power consumption; $P_D = C_{PD} \bullet V_{CC}^2 \bullet f_{in} + I_{CC} \bullet V_{CC}$.







*Includes all probe and jig capacitance. A 1–MHz square input wave is recommended for propagation delay tests.

Figure 5. Test Circuit

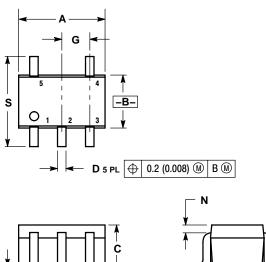
ORDERING INFORMATION

Device	Package	Shipping [†]
MC74VHC1GT00DFT1	SC70-5/SC-88A/SOT-353	
M74VHC1GT00DFT1G	SC70-5/SC-88A/SOT-353 (Pb-Free)	
MC74VHC1GT00DFT2	SC70-5/SC-88A/SOT-353	
M74VHC1GT00DFT2G	SC70-5/SC-88A/SOT-353 (Pb-Free)	3000/Tape & Reel
MC74VHC1GT00DTT1	SOT23-5/TSOP-5/SC59-5	
M74VHC1GT00DTT1G	SOT23–5/TSOP–5/SC59–5 (Pb–Free)	

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

PACKAGE DIMENSIONS

SC-88A, SOT-353, SC-70 CASE 419A-02 ISSUE J

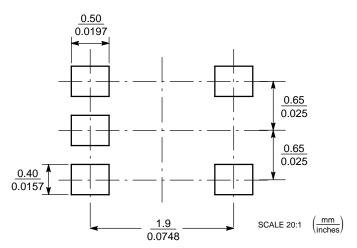


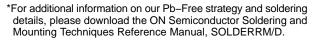
κ

NOTES: 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. 2. CONTROLLING DIMENSION: INCH. 3. 419A-01 OBSOLETE. NEW STANDARD 419A-02. 4. DIMENSIONS A AND B DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

	INC	HES	MILLIM	ETERS	
DIM	MIN	MAX	MIN	MAX	
Α	0.071	0.087	1.80	2.20	
В	0.045	0.053	1.15	1.35	
С	0.031	0.043	0.80	1.10	
D	0.004	0.012	0.10	0.30	
G	0.026	BSC	0.65 BSC		
Н		0.004		0.10	
ſ	0.004	0.010	0.10	0.25	
K	0.004	0.012	0.10	0.30	
Ν	0.008 REF		0.20	REF	
S	0.079	0.087	2.00	2.20	

SOLDERING FOOTPRINT*

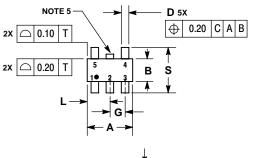


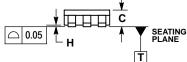


н

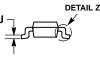
PACKAGE DIMENSIONS

TSOP-5 CASE 483-02 ISSUE F







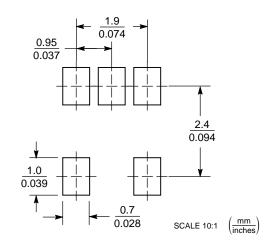


NOTES:

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
 CONTROLLING DIMENSION: MILLIMETERS.
- CONTROLLING DIMENSION: MILLIMETERS.
 MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
- DIMENSIONS A AND B DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.
- OPTIONAL CONSTRUCTION: AN ADDITIONAL TRIMMED LEAD IS ALLOWED IN THIS LOCATION. TRIMMED LEAD NOT TO EXTEND MORE THAN 0.2 FROM BODY.

	MILLIMETERS					
DIM	MIN MAX					
Α	3.00	BSC				
В	1.50	1.50 BSC				
С	0.90	1.10				
D	0.25	0.50				
G	0.95	0.95 BSC				
Н	0.01	0.10				
J	0.10	0.26				
ĸ	0.20	0.60				
L	1.25	1.55				
М	0 °	10 °				
S	2.50	3.00				

SOLDERING FOOTPRINT*



*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

ON Semiconductor and use registered trademarks of Semiconductor Components Industries, LLC (SCILLC). SCILLC reserves the right to make changes without further notice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use performance manufacture of the part. SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor P.O. Box 5163, Denver, Colorado 80217 USA Phone: 303–675–2175 or 800–344–3860 Toll Free USA/Canada Fax: 303–675–2176 or 800–344–3867 Toll Free USA/Canada Email: orderlit@onsemi.com N. American Technical Support: 800–282–9855 Toll Free USA/Canada Europe, Middle East and Africa Technical Support:

Phone: 421 33 790 2910 Japan Customer Focus Center Phone: 81–3–5773–3850 ON Semiconductor Website: www.onsemi.com

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative